RECTRON SEMICONDUCTOR
TECHNICAL SPECIFICATION

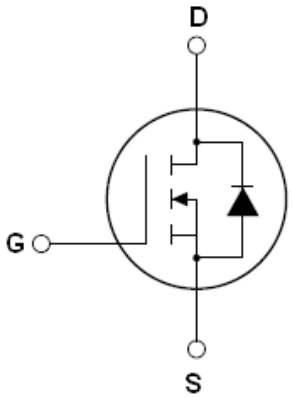
RM8N700LD(IP)

N-Channel Super Junction Power MOSFET Ⅲ

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

V_{DS}	700	V
$R_{DS(ON)TYP}$	540	mΩ
I_D	8	A



Schematic diagram

Features

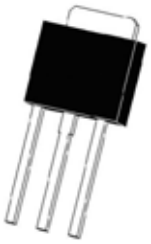
- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant
- Halogen-free

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）

Package Marking And Ordering Information

Device	Device Package	Marking
RM8N700IP	TO-251	8N700
RM8N700LD	TO-252	8N700



TO-251

TO-252

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	700	V
Gate-Source Voltage (V_{DS}=0V) ,AC (f>1 Hz)	V_{GS}	±30	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	8	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	5.2	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	32	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	69 0.55	W W/°C
Single pulse avalanche energy **(Note2)**	E_{AS}	156	mJ
Avalanche current **(Note 1)**	I_{AR}	1.7	A
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} **(Note 1)**	E_{AR}	0.3	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+150	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	1.81	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	700			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=700V,V_{GS}=0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=700V,V_{GS}=0V			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	3		4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=4A		540	600	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		590		pF
Output Capacitance	C_{oss}			37		pF
Reverse Transfer Capacitance	C_{rss}			0.9		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=8A, V_{GS}=10V		14.6	22	nC
Gate-Source Charge	Q_{gs}			4		nC
Gate-Drain Charge	Q_{gd}			6.7		nC
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=420V,I_D=4A, R_G=4.7Ω,V_{GS}=10V		9		nS
Turn-on Rise Time	t_r			6.5		nS
Turn-Off Delay Time	$t_{d(off)}$			61		nS
Turn-Off Fall Time	t_f			10		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			8	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				32	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=8A,V_{GS}=0V		0.9	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=4A,di/dt=100A/μs		230		nS
Reverse Recovery Charge	Q_{rr}			1.2		uC
Peak Reverse Recovery Current	I_{rrm}			10.5		A

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

RATING AND CHARACTERISTICS CURVES (RM8N700LD(IP))

Figure1. Safe operating area

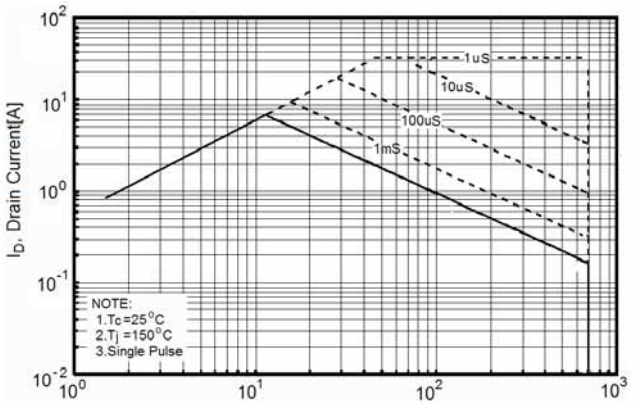


Figure2. Transient Thermal Impedance

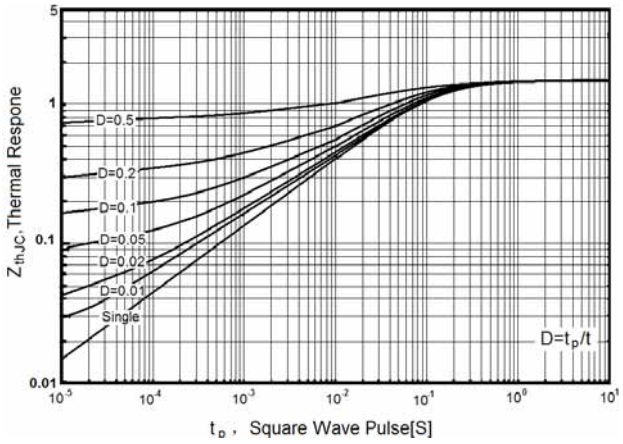


Figure3. Source-Drain Diode Forward Voltage

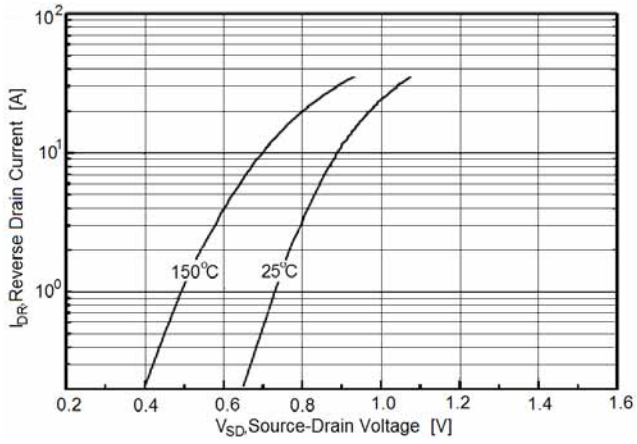


Figure4. Output characteristics

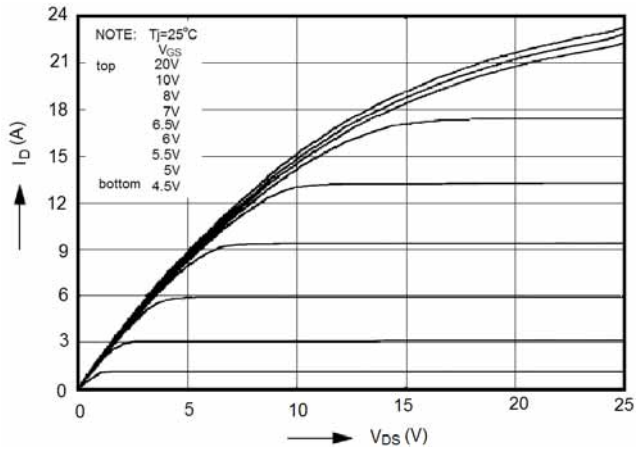


Figure5. Transfer characteristics

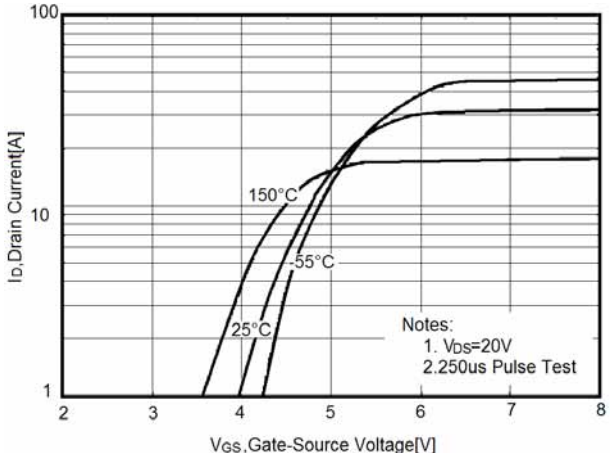


Figure6. Static drain-source on resistance

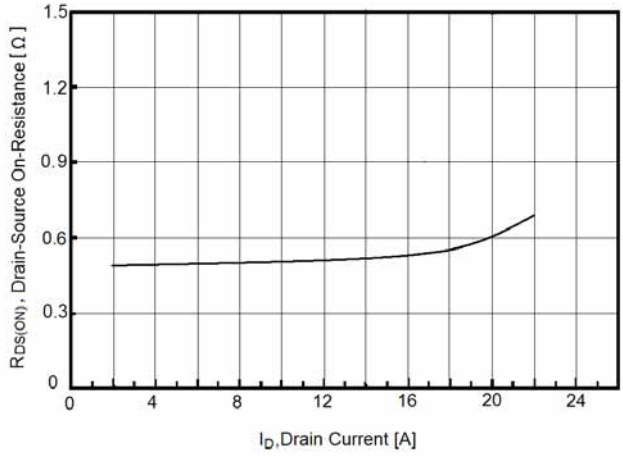


Figure7. $R_{DS(ON)}$ vs Junction Temperature

Figure8. BV_{DSS} vs Junction Temperature

RATING AND CHARACTERISTICS CURVES (RM8N700LD(IP))

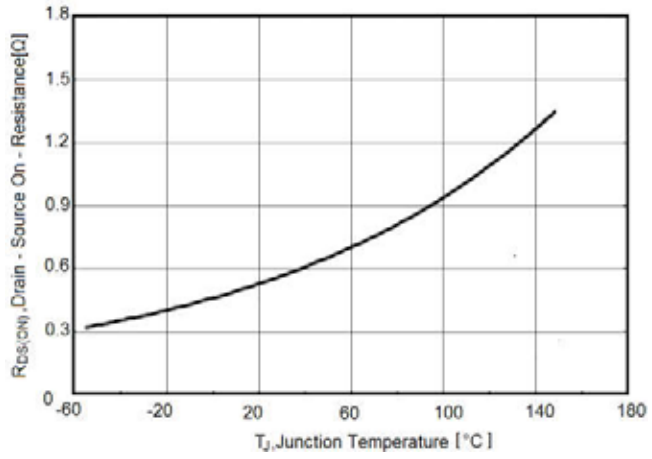


Figure9. Maximum I_D vs Junction Temperature

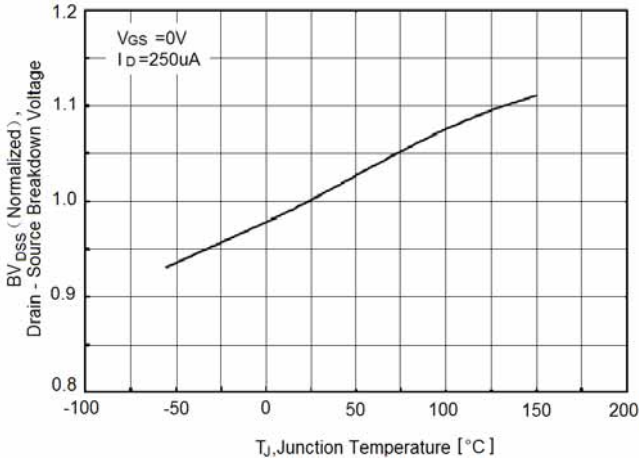
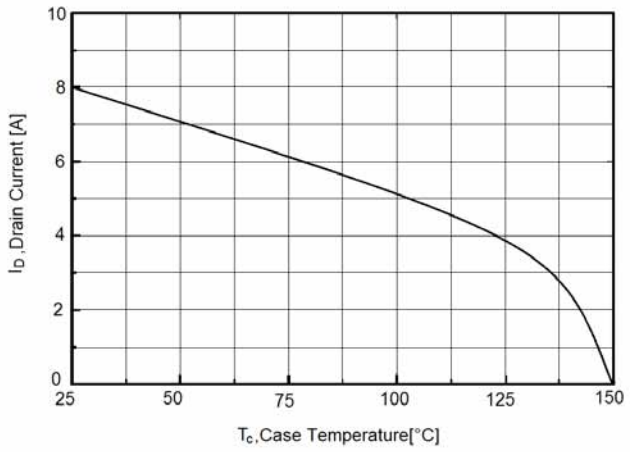


Figure10. Capacitance



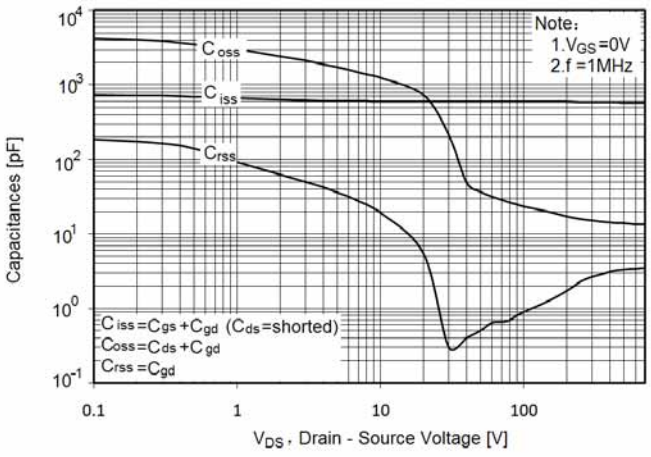
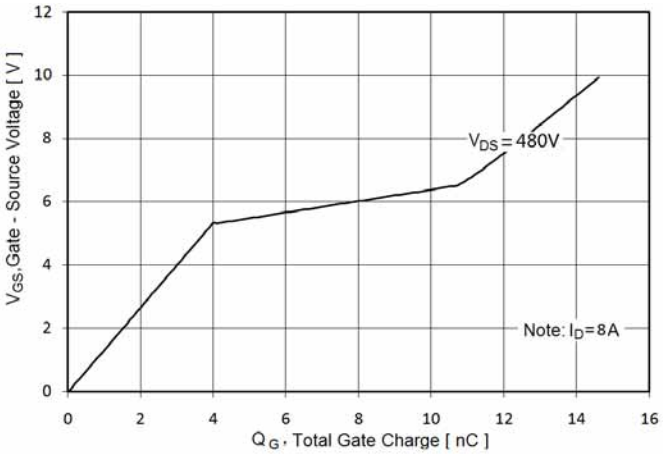
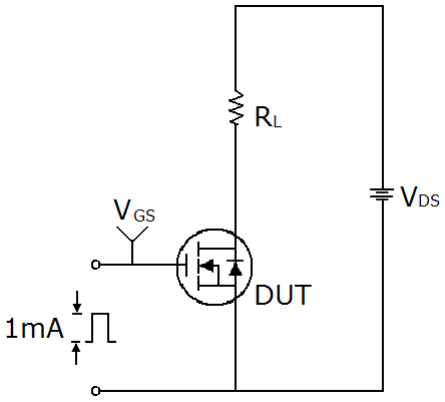


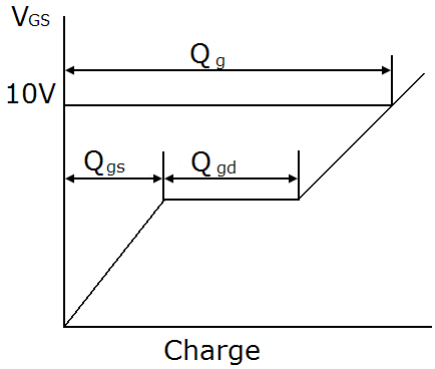
Figure11. Gate charge waveforms



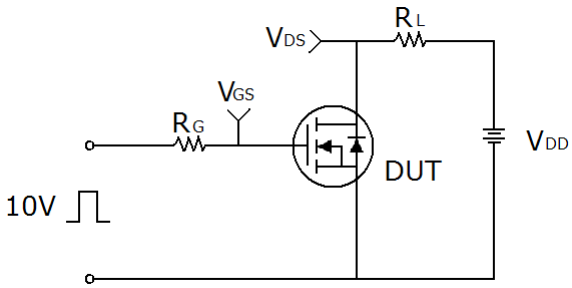
Test circuit

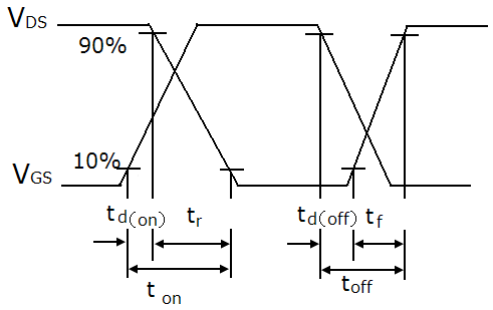
1）Gate charge test circuit & Waveform



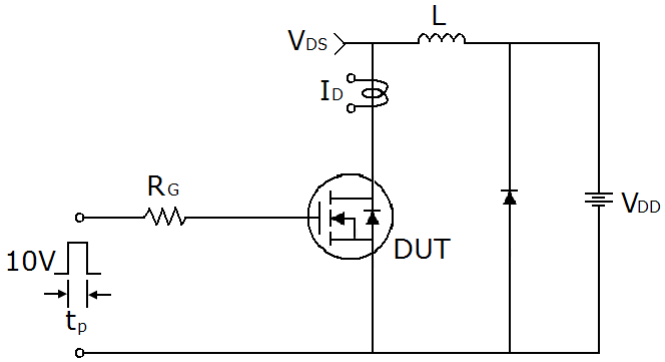


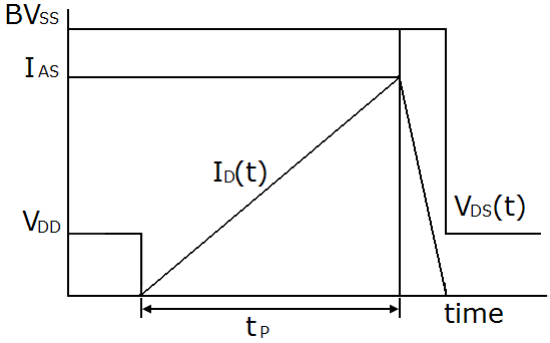
2）Switch Time Test Circuit:



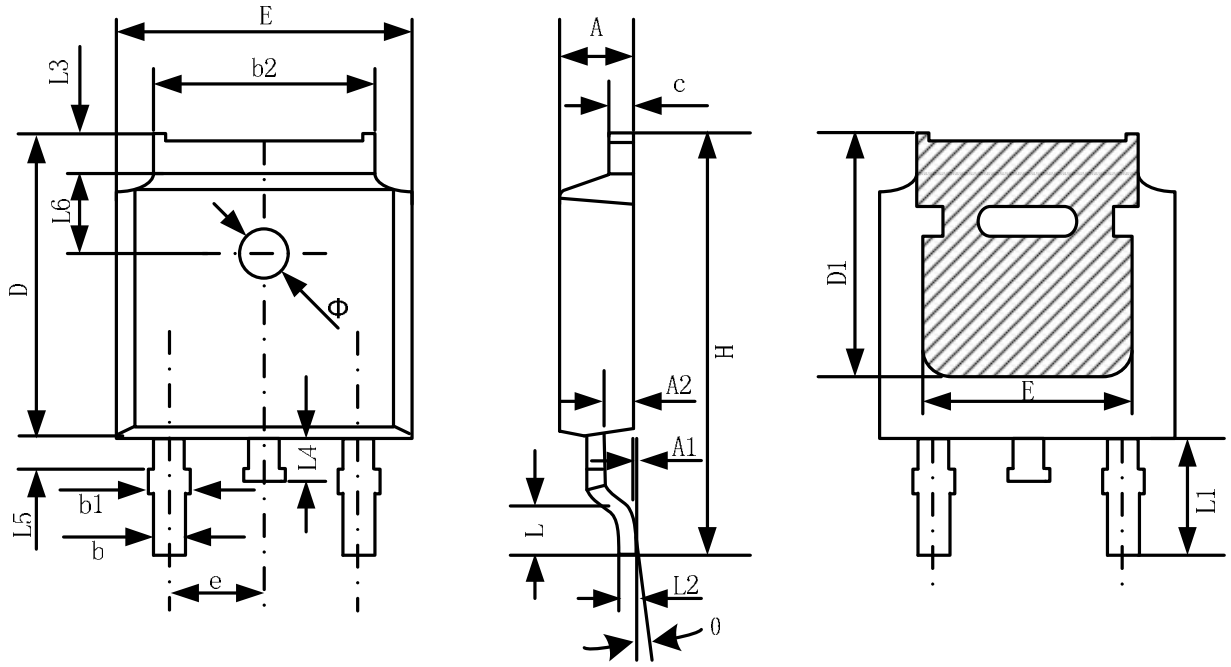


3）Unclamped Inductive Switching Test Circuit & Waveforms



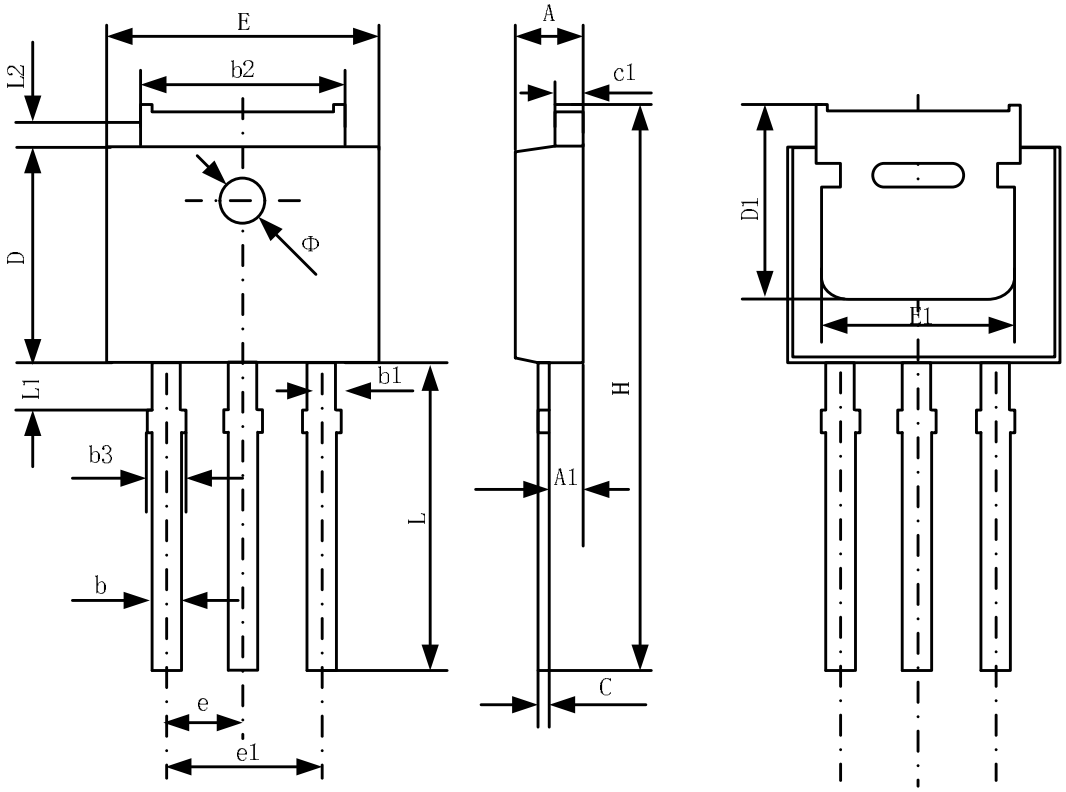


TO-252-2 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.38	0.087	0.094
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.043
b	0.72	0.85	0.028	0.033
b1	0.72	0.90	0.028	0.035
b2	5.13	5.46	0.202	0.215
c	0.47	0.60	0.019	0.024
D	6.00	6.20	0.236	0.244
D1	5.25	--	0.207	--
E	6.50	6.70	0.256	0.264
E1	4.70	--	0.185	--
e	2.19	2.39	0.086	0.094
H	9.80	10.40	0.386	0.409
L	1.40	1.70	0.055	0.067
L1	2.90 REF		0.114 REF	
L2	0.508 BSC		0.020 BSC	
L3	0.90	1.25	0.035	0.049
L4	0.60	1.00	0.024	0.039
L5	0.15	0.75	0.006	0.030
L6	1.80 REF		0.071 REF	
Φ	1.20	1.40	0.047	0.055
θ	0°	8°	0°	8°

TO-251 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.35	0.087	0.093
A1	0.90	1.10	0.035	0.043
b	0.56	0.69	0.022	0.027
b1	0.77	0.90	0.030	0.035
b2	5.23	5.43	0.206	0.214
b3		1.05	0.000	0.041
C	0.46	0.59	0.018	0.023
c1	0.46	0.59	0.018	0.023
D	6.00	6.20	0.236	0.244
D1	5.20		0.205	
E	6.50	6.70	0.256	0.264
E1	4.60	5.00	0.181	
e	2.24	2.34	0.088	0.092
e1	4.47	4.67	0.176	0.184
H	16.18	16.78	0.637	0.661
L	9.00	9.60	0.354	0.378
L1	0.95	1.35	0.037	0.053
L2	0.90	1.25	0.035	0.049

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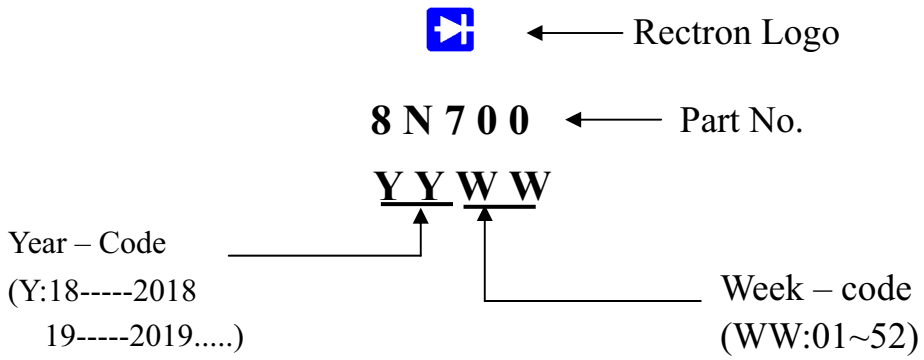
Marking on the body



	Package	Tube (pcs/tube)	Tube (pcs/inner box)	Tube (pcs/cartoon)	Tape&Reel (pcs/reel)	Tape&Reel (pcs/inner box)	Tape&Reel (pcs/cartoon)
	DFN	100	10,000	100,000	2,500	5,000	40,000
	SOP-8	100	10,000	100,000	4,000	4,000	20,000
	TSSOP-8	100	32,000	128,000	3,000	6,000	48,000
	SOT-23-3L	——	——	——	3,000	30,000	120,000
	SOT-23-6L	——	——	——	3,000	30,000	120,000
	SOT-23(6R)	——	——	——	3,000	30,000	120,000
	SOT-363	——	——	——	3,000	30,000	120,000
	SOT-523	——	——	——	3,000	30,000	120,000
	TO-220	50	1,000	5,000	——	——	——
	TO-220F	50	1,000	10,000	——	——	——
	TO-247	30	300	1,200	——	——	——
	TO-251	80	4,000	40,000	——	——	——
	TO-251S(4R)	80	4,000	40,000	——	——	——
	TO-252-2L(4R)	80	4,000	40,000	2,500	2,500	25,000
	TO-263-2L	50	1,000	10,000	800	800	8,000
	TO-3P	30	300	3,000	——	——	——
	TO-92	——	——	——	1,000(袋装)	10,000	100,000

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